ABSTRACT

LASER PROCESSING METHOD

There is provided a laser processing method of laser-processing a wafer along a plurality of streets formed in a lattice manner on a top surface of the wafer, the wafer having devices formed in a plurality of regions partitioned by the streets, the laser processing method including: a wafer holding step of holding an undersurface of the wafer by a chuck table; a resin supplying step of supplying a water-soluble liquid resin to the top surface of the wafer; a protective film forming step of forming a protective film P on the wafer as a result of drying the water-soluble liquid resin by irradiating the water-soluble liquid resin with light from a xenon flash lamp; a laser irradiating step of irradiating the wafer with a laser beam through the protective film along the streets; and a cleaning step of cleaning the wafer after the laser irradiating step.

(Figure 5)